# +175°C P-CHANNEL ENHANCEMENT MODE MOSFET

## Product Summary

| $BV_{DSS}$ | $R_{DS(ON)}$ Max | $I_D$ $T_C$ = +25°C |
|---|---|---|
| -40V | 11mΩ @ $V_{GS}$ = -10V | -45A |
| | 15mΩ @ $V_{GS}$ = -4.5V | -40A |

## Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMPH4015SK3Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

  **https://www.diodes.com/quality/product-definitions/**

## Description and Applications

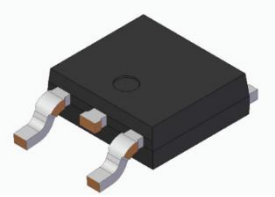
This MOSFET has been designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Reverse-polarity protections
- Motor control
- Power management

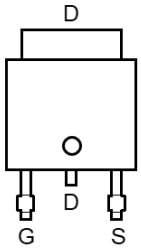
## Mechanical Data

- Package: TO252
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.33 grams (Approximate)

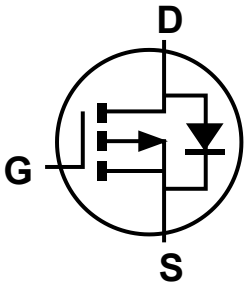
TO252 (DPAK)



Top View




Top View
Pinout



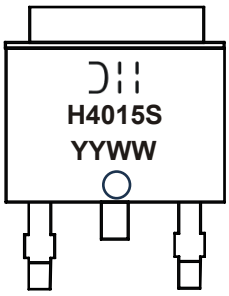

Equivalent Circuit

## Ordering Information (Note 4)

| Orderable Part Number | Package | Packing | |
|---|---|---|---|
| | | Qty. | Carrier |
| DMPH4015SK3Q-13 | TO252 (DPAK) | 2,500 | Tape & Reel |

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## Marking Information




= Manufacturer's Marking
H4015S = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 26 = 2026)
WW = Week (01 to 53)


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## Maximum Ratings (@ $T_A$ = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|---|---|---|---|---|---|
| Drain-Source Voltage | | | $V_{DSS}$ | -40 | V |
| Gate-Source Voltage | | | $V_{GSS}$ | ±25 | V |
| Continuous Drain Current (Note 6) $V_{GS}$ = -10V | Steady State | $T_C$ = +25°C<br>$T_C$ = +100°C | $I_D$ | -45<br>-35 | A |
| | Steady State | $T_A$ = +25°C<br>$T_A$ = +100°C | $I_D$ | -14<br>-10 | A |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | | | $I_{DM}$ | -100 | A |
| Maximum Body Diode Forward Current (Note 6) | | | $I_S$ | -45 | A |
| Avalanche Current, L = 1mH (Note 7) | | | $I_{AS}$ | -22 | A |
| Avalanche Energy, L = 1mH (Note 7) | | | $E_{AS}$ | 260 | mJ |

## Thermal Characteristics (@ $T_A$ = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit |
|---|---|---|---|---|
| Total Power Dissipation (Note 5) | | $P_D$ | 1.7 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | $R_{\theta JA}$ | 73 | °C/W |
| Total Power Dissipation (Note 6) | | $P_D$ | 3.3 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | $R_{\theta JA}$ | 38 | °C/W |
| Thermal Resistance, Junction to Case | | $R_{\theta JC}$ | 1.0 | |
| Operating and Storage Temperature Range | | $T_J$, $T_{STG}$ | -55 to +175 | °C |

## Electrical Characteristics (@ $T_A$ = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS (Note 8)** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | -40 | — | — | V | $V_{GS}$ = 0, $I_D$ = -250µA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | — | — | -1 | µA | $V_{DS}$ = -40V, $V_{GS}$ = 0 |
| Gate-Source Leakage | $I_{GSS}$ | — | — | ±100 | nA | $V_{GS}$ = ±25V, $V_{DS}$ = 0 |
| **ON CHARACTERISTICS (Note 8)** | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | -1.5 | -2 | -2.5 | V | $V_{DS}$ = $V_{GS}$, $I_D$ = -250µA |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | — | 8 | 11 | mΩ | $V_{GS}$ = -10V, $I_D$ = -9.8A |
| | | — | 11 | 15 | | $V_{GS}$ = -4.5V, $I_D$ = -9.8A |
| Diode Forward Voltage | $V_{SD}$ | — | -0.7 | -1 | V | $V_{GS}$ = 0, $I_S$ = -1A |
| **DYNAMIC CHARACTERISTICS (Note 9)** | | | | | | |
| Input Capacitance | $C_{iss}$ | — | 4234 | — | pF | $V_{DS}$ = -20V, $V_{GS}$ = 0<br>f = 1MHz |
| Output Capacitance | $C_{oss}$ | — | 1036 | — | | |
| Reverse Transfer Capacitance | $C_{rss}$ | — | 526 | — | | |
| Gate Resistance | $R_g$ | — | 7.8 | — | Ω | $V_{DS}$ = 0, $V_{GS}$ = 0, f = 1MHz |
| Total Gate Charge ($V_{GS}$ = -4.5V) | $Q_g$ | — | 42.7 | — | nC | $V_{DS}$ = -20V,<br>$I_D$ = -9.8A |
| Total Gate Charge ($V_{GS}$ = -10V) | $Q_g$ | — | 91 | — | | |
| Gate-Source Charge | $Q_{gs}$ | — | 14.2 | — | | |
| Gate-Drain Charge | $Q_{gd}$ | — | 13.5 | — | | |
| Turn-On Delay Time | $t_{D(ON)}$ | — | 13.2 | — | ns | $V_{GS}$ = -10V, $V_{DD}$ = -20V,<br>$R_G$ = 6Ω, $I_D$ = -1A |
| Turn-On Rise Time | $t_R$ | — | 10 | — | | |
| Turn-Off Delay Time | $t_{D(OFF)}$ | — | 303 | — | | |
| Turn-Off Fall Time | $t_F$ | — | 138 | — | | |
| Reverse-Recovery Time | $t_{RR}$ | — | 26 | — | ns | $I_F$ = -9.8A, di/dt = -100A/µs |
| Reverse-Recovery Charge | $Q_{RR}$ | — | 20 | — | nC | $I_F$ = -9.8A, di/dt = -100A/µs |

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. $I_{AS}$ and $E_{AS}$ ratings are based on low frequency and duty cycles to keep $T_J$ = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.


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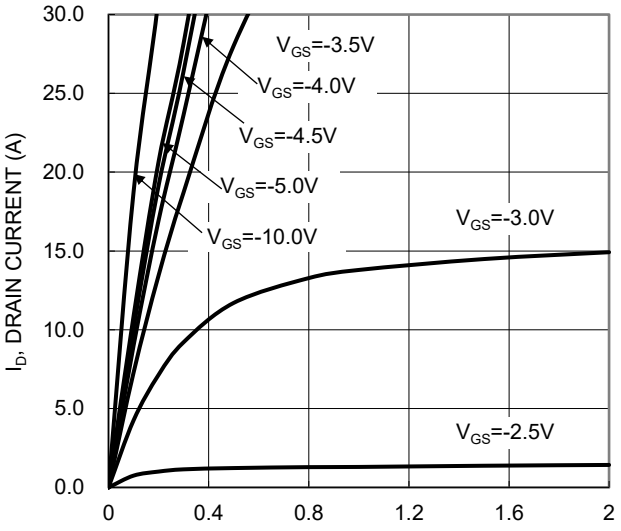



Figure 1. Typical Output Characteristic

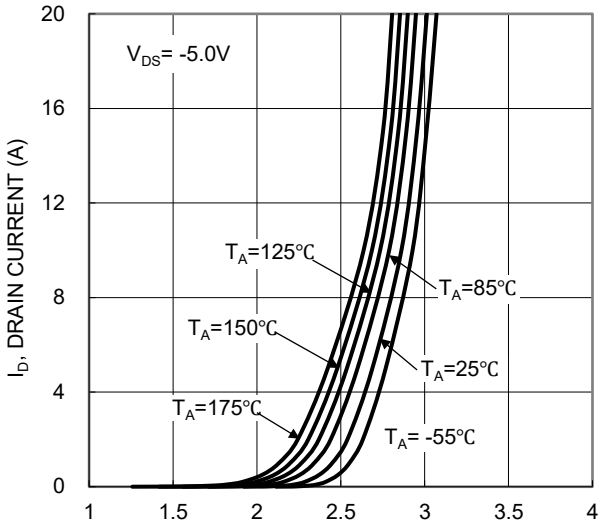



Figure 2. Typical Transfer Characteristic

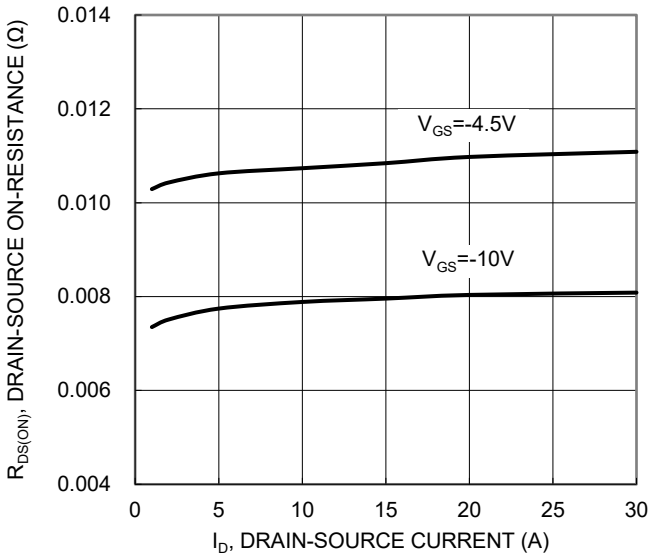



Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

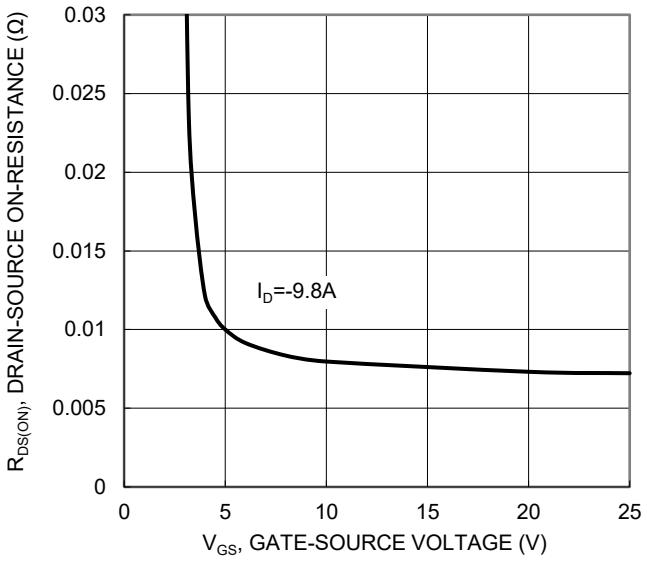



Figure 4. Typical Transfer Characteristic

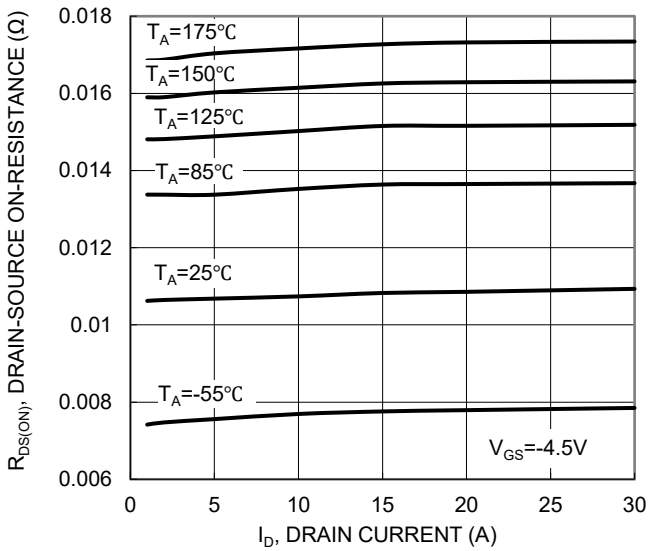



Figure 5. Typical On-Resistance vs. Drain Current and Temperature

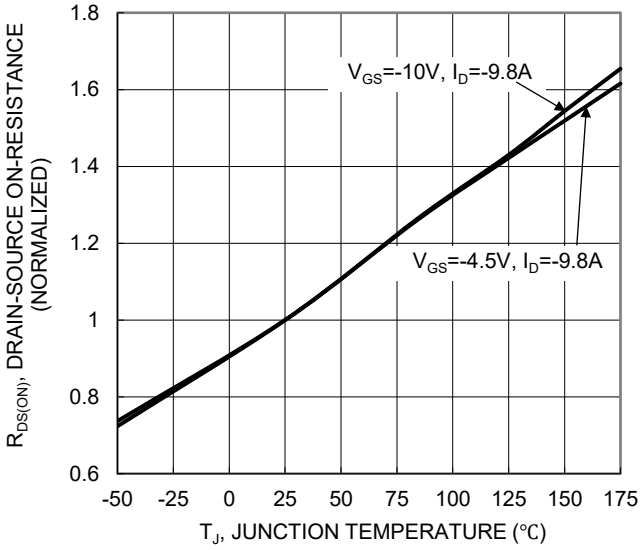



Figure 6. On-Resistance Variation with Temperature


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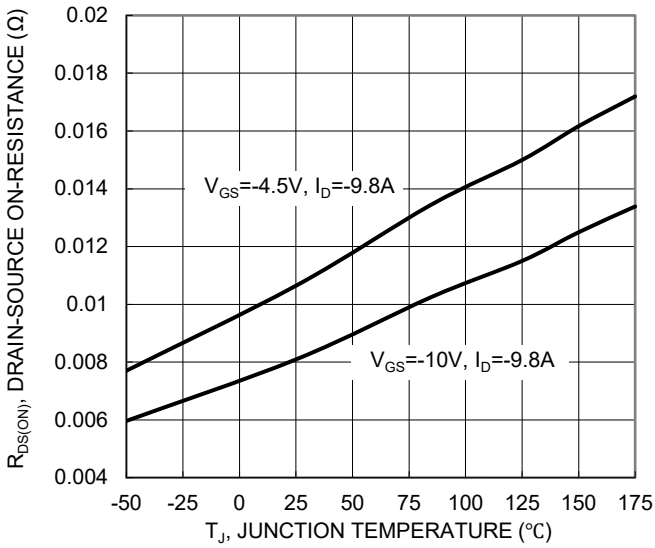



Figure 7. On-Resistance Variation with Temperature

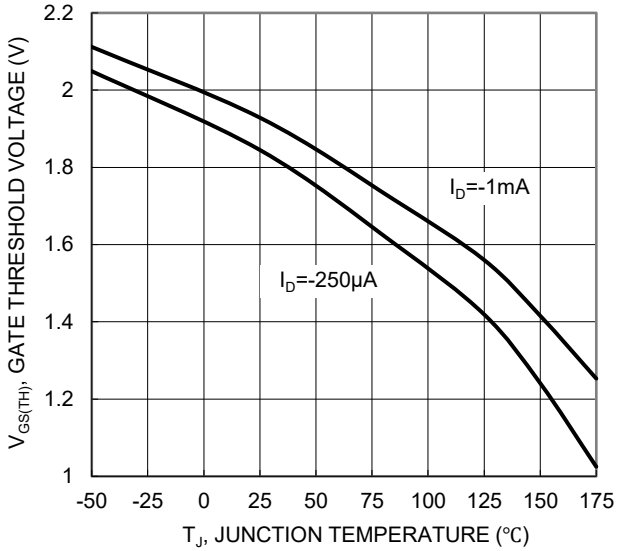



Figure 8. Gate Threshold Variation vs Temperature

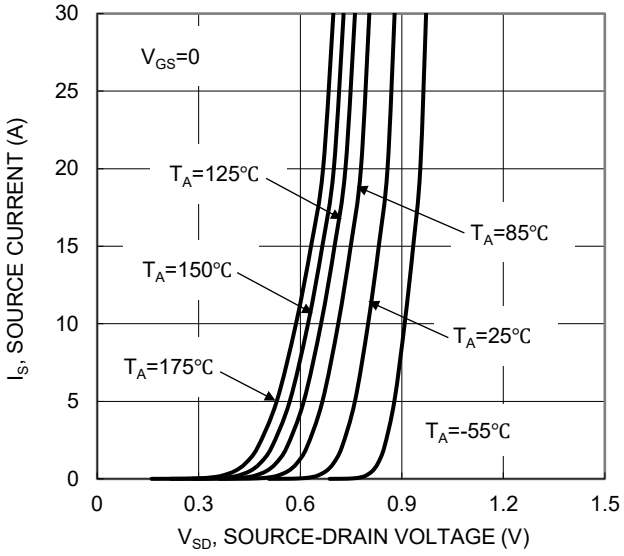



Figure 9. Diode Forward Voltage vs. Current

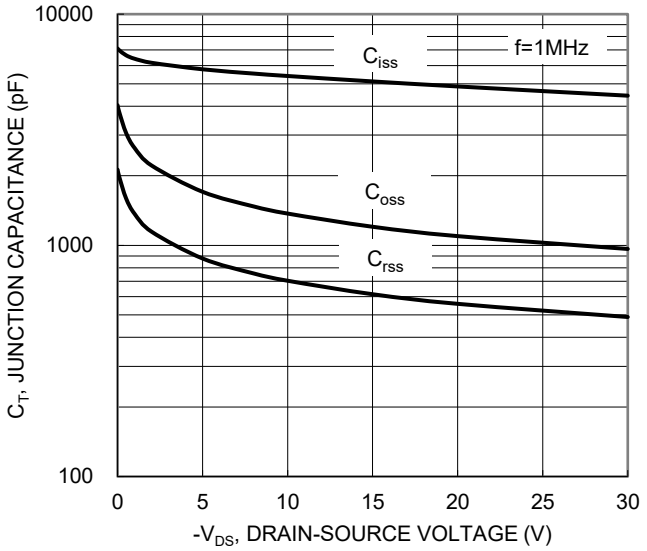



Figure 10. Typical Junction Capacitance

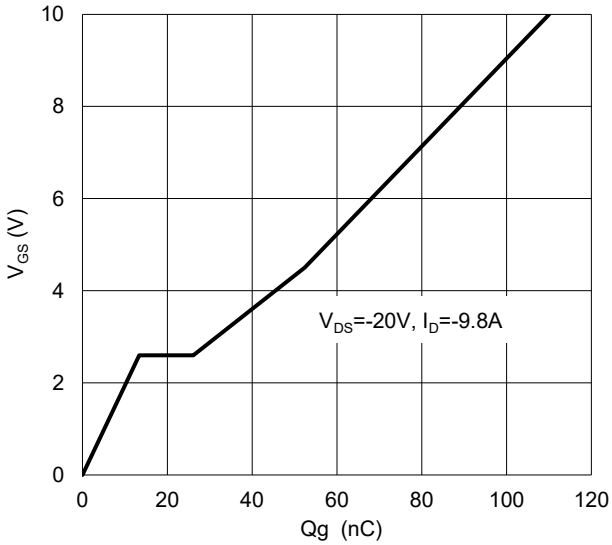



Figure 11. Gate Charge

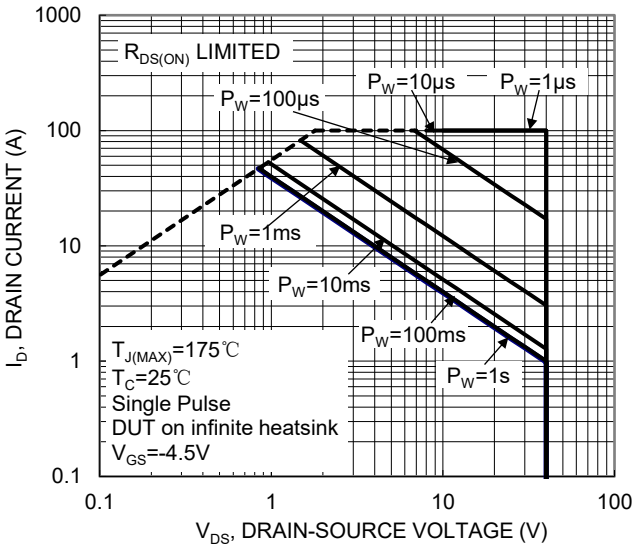



Figure 12. SOA, Safe Operation Area


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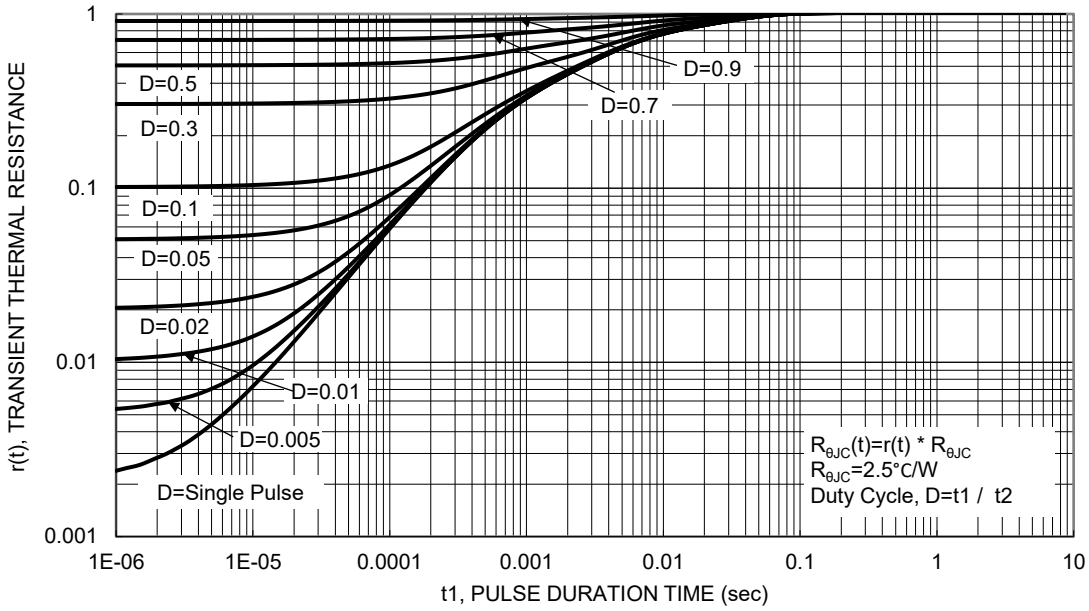


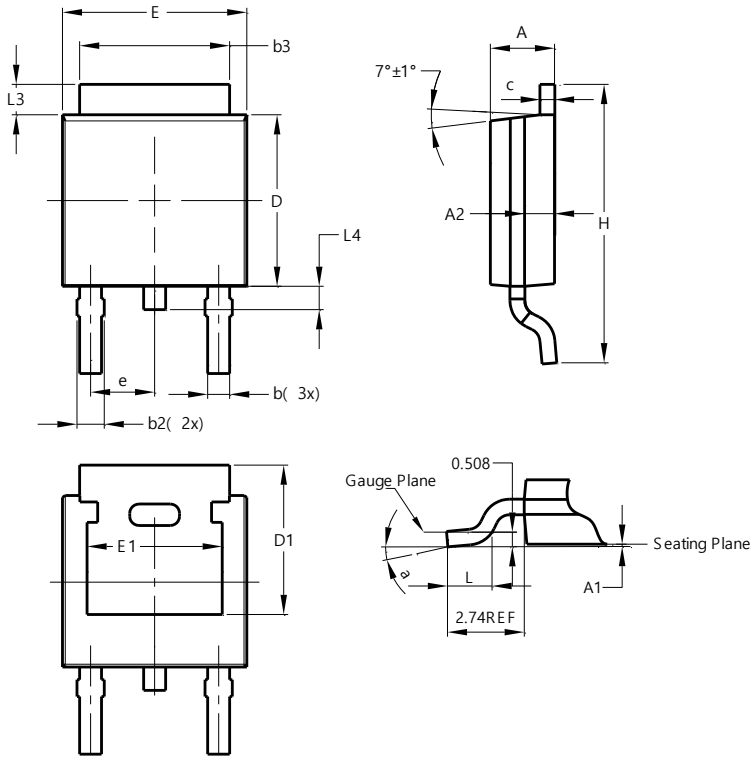

Figure 13. Transient Thermal Resistance


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## Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

**TO252 (DPAK)**

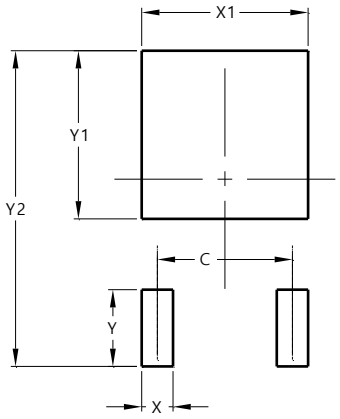



| TO252 (DPAK) | | | |
|---|---|---|---|
| **Dim** | **Min** | **Max** | **Typ** |
| **A** | 2.19 | 2.39 | 2.29 |
| **A1** | 0.00 | 0.13 | 0.08 |
| **A2** | 0.97 | 1.17 | 1.07 |
| **b** | 0.64 | 0.88 | 0.783 |
| **b2** | 0.76 | 1.14 | 0.95 |
| **b3** | 5.21 | 5.50 | 5.33 |
| **c** | 0.45 | 0.58 | 0.531 |
| **D** | 6.00 | 6.20 | 6.10 |
| **D1** | 5.21 | -- | -- |
| **e** | 2.286 BSC | | |
| **E** | 6.45 | 6.70 | 6.58 |
| **E1** | 4.32 | -- | -- |
| **H** | 9.40 | 10.41 | 9.91 |
| **L** | 1.40 | 1.78 | 1.59 |
| **L3** | 0.88 | 1.27 | 1.08 |
| **L4** | 0.64 | 1.02 | 0.83 |
| **a** | 0° | 10° | -- |
| **All Dimensions in mm** | | | |

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

**TO252 (DPAK)**




| Dimensions | Value (in mm) |
|---|---|
| **C** | 4.572 |
| **X** | 1.060 |
| **X1** | 5.632 |
| **Y** | 2.600 |
| **Y1** | 5.700 |
| **Y2** | 10.700 |


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